



Best $R_{DS(on)}$ * Q_g

STP20NM50FD STB20NM50FD-1

N-CHANNEL 500V - 0.22Ω - 20A TO-220/I²PAK
FDmesh™ Power MOSFET (with FAST DIODE)

TYPE	V _{DSS}	R _{DS(on)}	R _{DS(on)} *Q _g	I _D
STP20NM50FD	500V	<0.25Ω	8.36 Ω*nC	20 A
STB20NM50FD-1	500V	<0.25Ω	8.36 Ω*nC	20 A

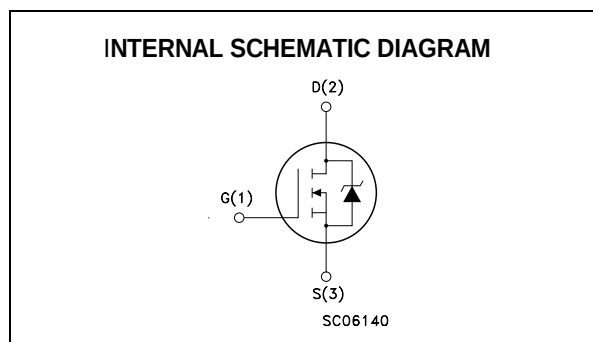
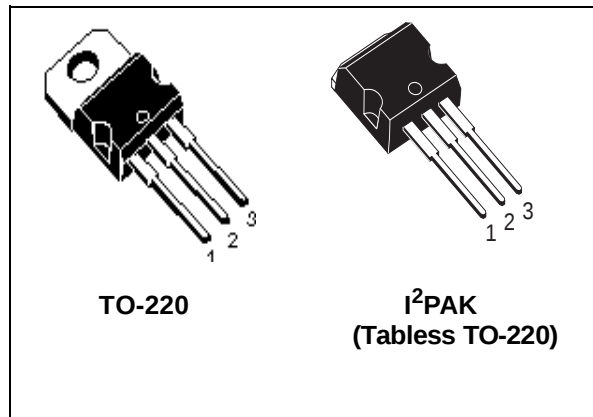
- TYPICAL R_{DS(on)} = 0.22Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS

DESCRIPTION

The FDmesh™ associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

APPLICATIONS

- ZVS PHASE-SHIFT FULL BRIDGE CONVERTERS FOR SMPS AND WELDING EQUIPMENT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate- source Voltage	±30	V
I _D	Drain Current (continuos) at T _C = 25°C	20	A
I _D	Drain Current (continuos) at T _C = 100°C	14	A
I _{DM} (●)	Drain Current (pulsed)	80	A
P _{TOT}	Total Dissipation at T _C = 25°C	192	W
	Derating Factor	1.2	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	20	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*)Pulse width limited by safe operating area

(1)I_{SD} ≤ 20A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

(*)Limited only by maximum temperature allowed

STP20NM50FD/STB20NM50FD-1

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.65	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	10	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 35 V)	700	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 10A		0.22	0.25	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 10A		9		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1380		pF
C _{oss}	Output Capacitance			290		pF
C _{rss}	Reverse Transfer Capacitance			40		pF
C _{oss eq.} (2)	Equivalent Output Capacitance	V _{GS} = 0V, V _{DS} = 0V to 400V		130		pF
R _g	Gate Input Resistance	f=1 MHz Gate DC Bias=0 Test Signal Level=20mV Open Drain		2.8		Ω

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.

2. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 250V, I_D = 10A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		22		ns
t_r	Rise Time			20		ns
Q_g	Total Gate Charge	$V_{DD} = 400V, I_D = 20A,$ $V_{GS} = 10V$		38	53	nC
Q_{gs}	Gate-Source Charge			18		nC
Q_{gd}	Gate-Drain Charge			10		nC

SWITCHING OFF

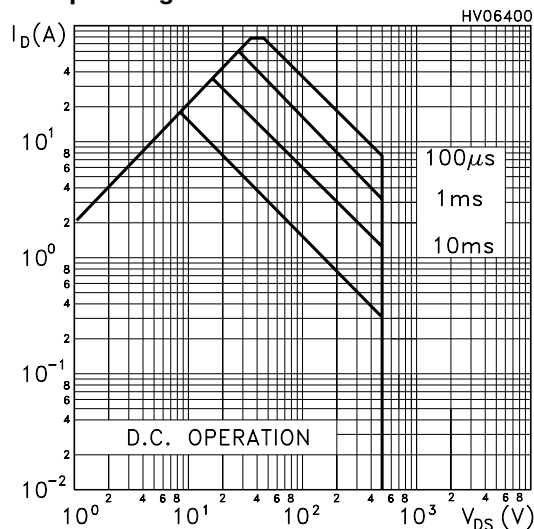
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400V, I_D = 20A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		6		ns
t_f	Fall Time			15		ns
t_c	Cross-over Time			30		ns

SOURCE DRAIN DIODE

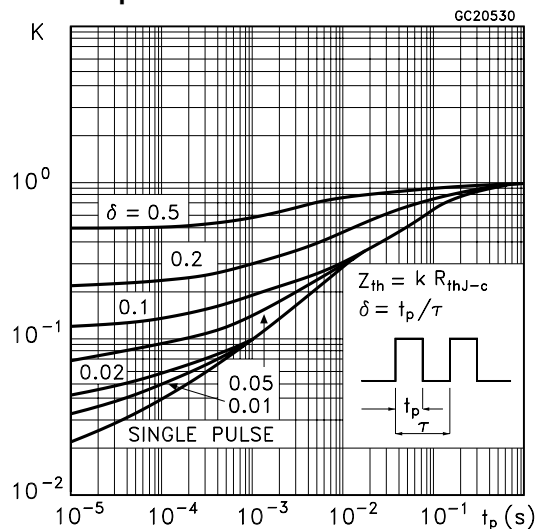
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				20	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				80	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 20A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 20A, di/dt = 100A/\mu s,$ $V_{DD} = 60V, T_J = 150^\circ C$ (see test circuit, Figure 5)		245		ns
Q_{rr}	Reverse Recovery Charge			2		μC
I_{RRM}	Reverse Recovery Current			16		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

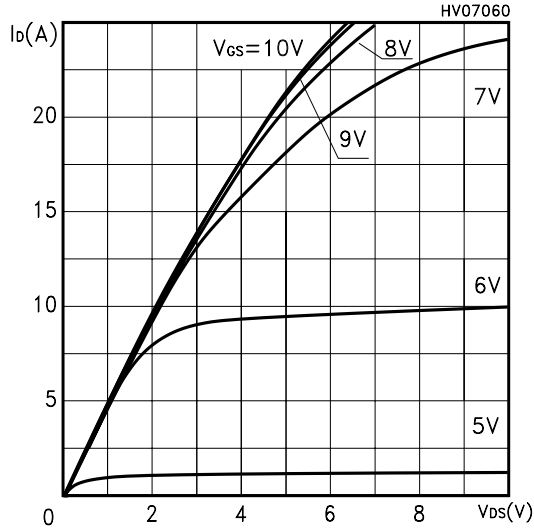
Safe Operating Area For TO-220 / I²PAK



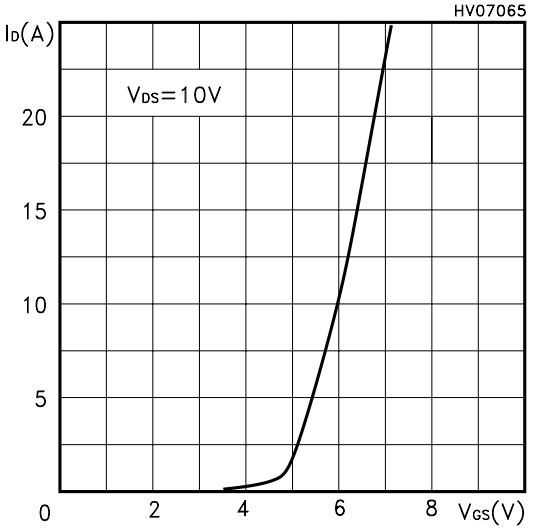
Thermal Impedance For TO-220 / I²PAK



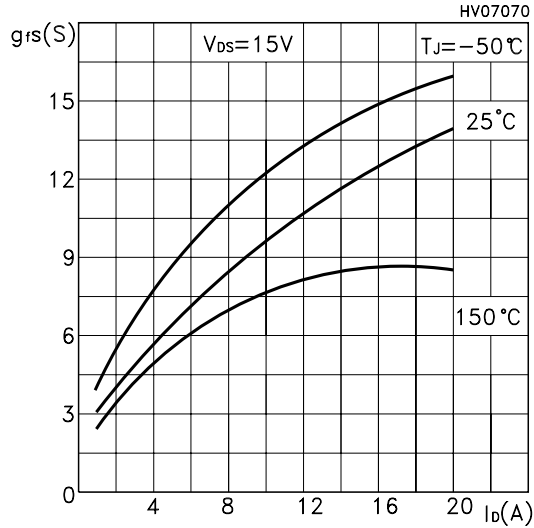
Output Characteristics



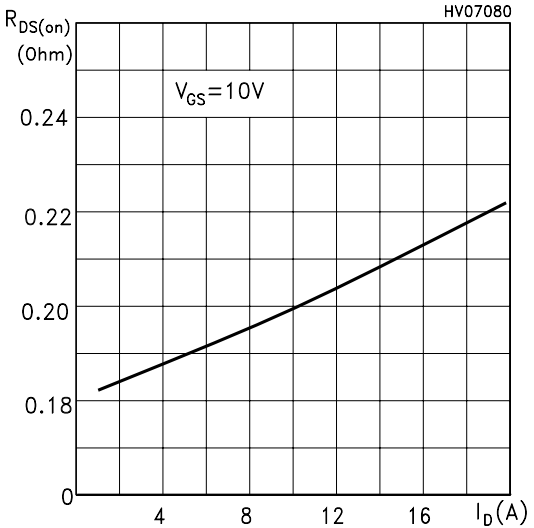
Transfer Characteristics



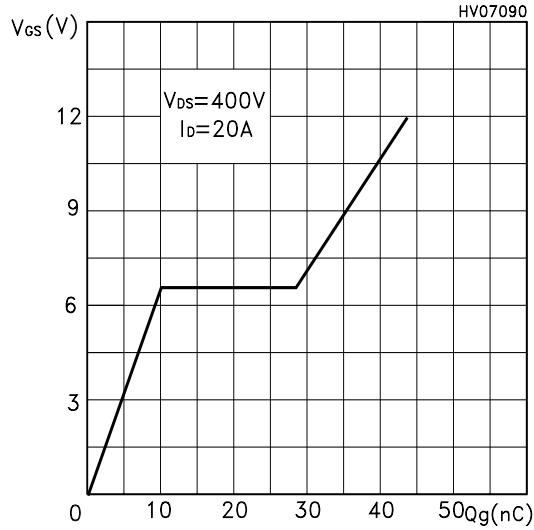
Transconductance



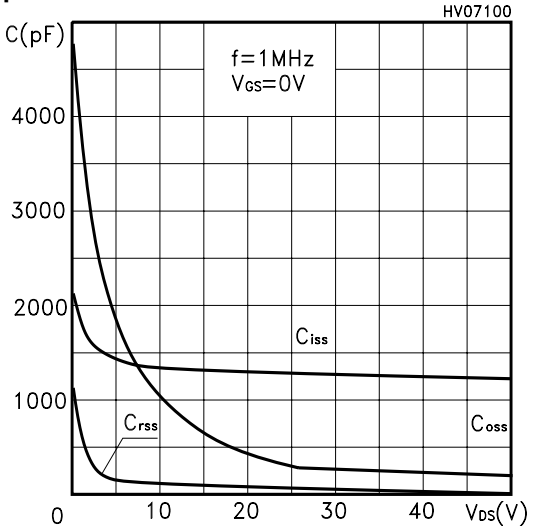
Static Drain-source On Resistance



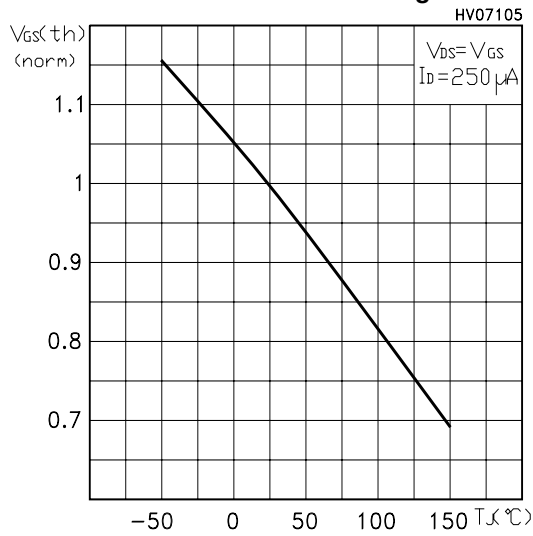
Gate Charge vs Gate-source Voltage



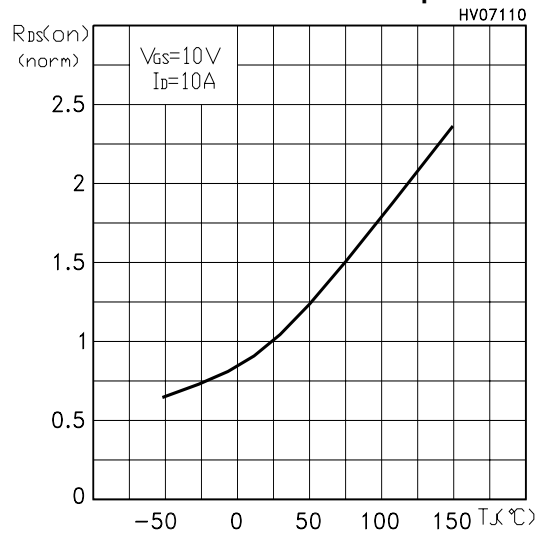
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

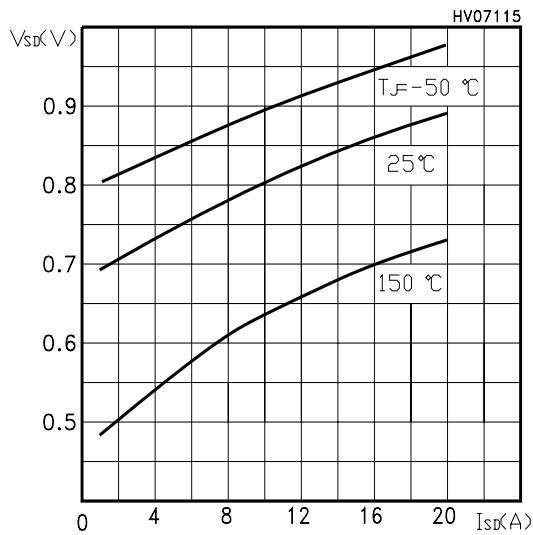


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load

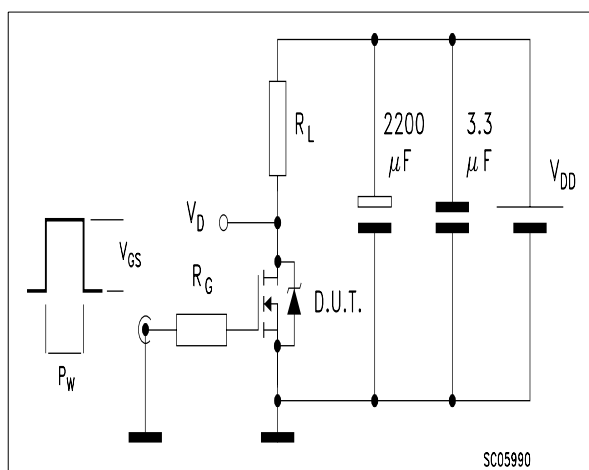


Fig. 4: Gate Charge test Circuit

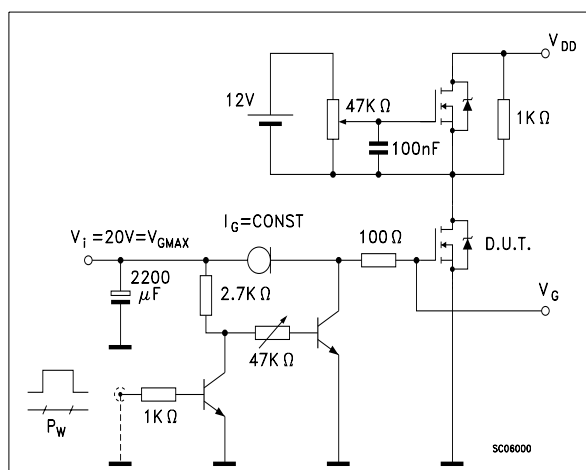
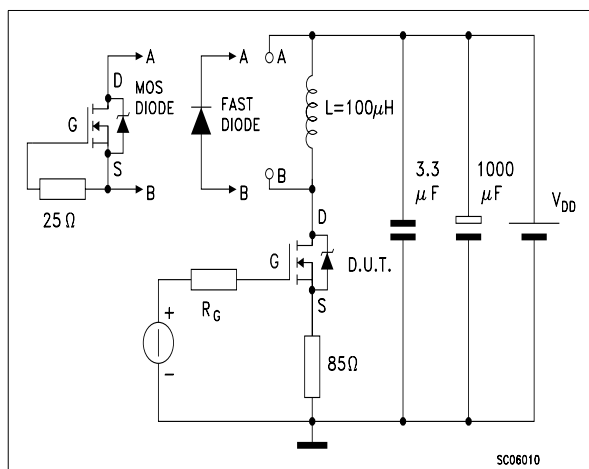
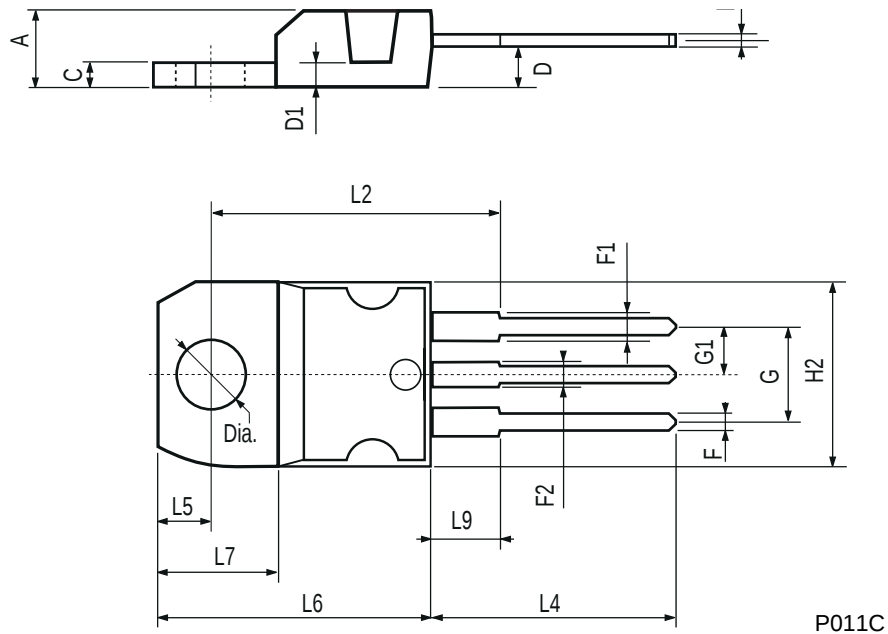


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



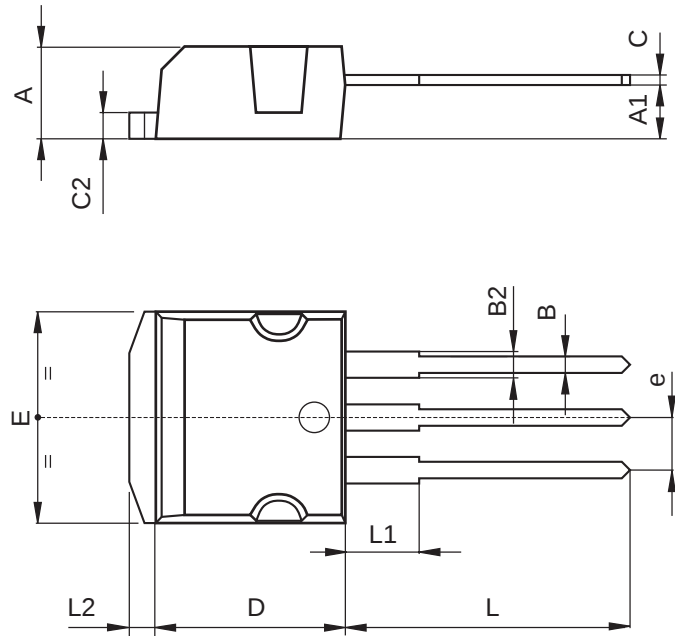
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055



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